TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

# **TC74VCXH16245FT**

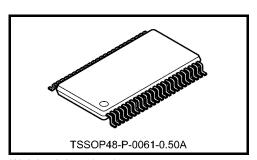
#### Low-Voltage 16-Bit Bus Transceiver with Bushold

The TC74VCXH16245FT is a high-performance CMOS 16-bit bus transceiver. Designed for use in 1.8-V, 2.5-V or 3.3-V systems, it achieves high-speed operation while maintaining the CMOS low power dissipation.

This 16-bit bus transceiver is controlled by direction control (DIR) inputs and output enable ( $\overline{\text{OE}}$ ) inputs which are common to each byte. It can be used as two 8-bit transceivers or one 16-bit transceiver. The direction of data transmission is determined by the level of the DIR inputs. The  $\overline{\text{OE}}$  inputs can be used to disable the device so that the busses are effectively isolated.

The A, B data inputs include active bushold circuitry, eliminating the need for external pull-up resisisors to hold unused or floating data inputs at a valid logic level.

All inputs are equipped with protection circuits against static discharge.



Weight: 0.25 g (typ.)

#### Features (Note)

- Low-voltage operation: V<sub>CC</sub> = 1.8 to 3.6 V
- Bushold on data inputs eliminating the need for external pull-up/pull-down resistors
- High-speed operation: t<sub>pd</sub> = 2.5 ns (max) (V<sub>CC</sub> = 3.0 to 3.6 V)

:  $t_{pd}$  = 3.0 ns (max) ( $V_{CC}$  = 2.3 to 2.7 V)

 $: t_{pd} = 5.0 \text{ ns (max) (V}_{CC} = 1.8 \text{ V)}$ 

- 3.6-V tolerant control inputs
- Output current: I<sub>OH</sub>/I<sub>OL</sub> = ±24 mA (min) (V<sub>CC</sub> = 3.0 V)

 $: I_{OH}/I_{OL} = \pm 18 \text{ mA (min)} (V_{CC} = 2.3 \text{ V})$ 

 $: I_{OH}/I_{OL} = \pm 6 \text{ mA (min)} (V_{CC} = 1.8 \text{ V})$ 

- Latch-up performance: -300 mA
- ESD performance: Machine model ≥ ±200 V

Human body model ≥ ±2000 V

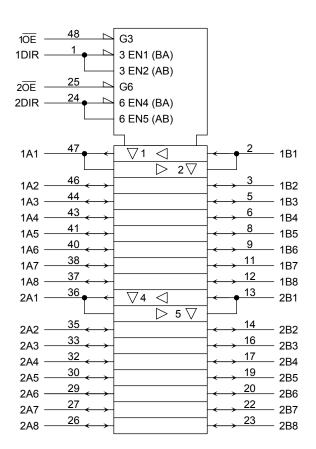
Package: TSSOP

Note: Do not apply a signal to any bus pins when it is in the output mode. Damage may result.

### Pin Assignment (top view)

#### 1DIR 10E 48 1B1 47 1A1 1B2 3 46 1A2 GND 4 45 **GND** 1B3 5 1A3 6 1B4 43 1A4 $V_{CC}$ 7 42 $V_{CC}$ 1B5 8 1A5 41 9 1B6 40 1A6 GND 10 39 **GND** 1B7 11 38 1A7 1B8 12 37 1A8 2B1 13 36 2A1 2B2 14 35 2A2 GND 15 GND 34 2B3 16 33 2A3 2B4 17 32 2A4 V<sub>CC</sub> 18 31 $V_{CC}$ 2B5 19 30 2A5 2B6 20 29 2A6 GND 21 28 GND 2B7 22 2A7 27 2B8 23 2A8 26 2OE 2DIR 24 25

### **IEC Logic Symbol**



### **Truth Table**

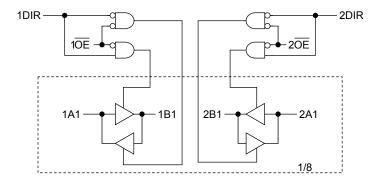
Inp	uts	Fun		
1OE	1DIR	Bus 1A1-1A8	Bus 1B1-1B8	Outputs
L	L	Output	Input	A = B
L	Н	Input	Output	B = A
Н	Х	Z		Z

Inp	uts	Fun	ction	
2 <del>OE</del>	2DIR	Bus 2A1-2A8	Bus 2B1-2B8	Outputs
L	L	Output	Input	A = B
L	Н	Input	Output	B=A
Н	Х	Z		Z

X: Don't care

Z: High impedance

### **System Diagram**



### **Absolute Maximum Ratings (Note 1)**

Characteristics		Symbol	Rating	Unit	
Power supply voltage		$V_{CC}$	-0.5 to 4.6	V	
	(DIR, OE)		-0.5 to 4.6		
DC input voltage	(An, Bn)	$V_{IN}$	-0.5 to V <sub>CC</sub> + 0.5	V	
			(Note 2)		
DC output voltage	(An, Bn)	V <sub>OUT</sub>	$-0.5$ to $V_{CC} + 0.5$	V	
DC output voltage	(All, Bll)	٧٥٥١	(Note 3)	V	
Input diode current		I <sub>IK</sub>	-50	mA	
Output diode current		I <sub>OK</sub>	±50 (Note 4)	mA	
Output current		lout	±50	mA	
Power dissipation		$P_{D}$	400	mW	
DC V <sub>CC</sub> /ground current per supply pin		I <sub>CC</sub> /I <sub>GND</sub>	±100	mA	
Storage temperature		T <sub>stg</sub>	-65 to 150	°C	

Note 1: Exceeding any of the absolute maximum ratings, even briefly, lead to deterioration in IC performance or even destruction.

Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings and the operating ranges.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 2: OFF state

Note 3: High or low state. IOUT absolute maximum rating must be observed.

Note 4: Vout < GND, Vout > Vcc

#### **Operating Ranges (Note 1) (Note 2)**

Characteristics		Symbol	Rating	Unit
Power supply voltage		V <sub>CC</sub>	1.8 to 3.6	V
1 ower supply voltage		vCC	1.2 to 3.6 (Note 3)	V
Input voltage	(DIR, OE)	\/	-0.3 to 3.6	V
input voitage	(An, Bn)	V <sub>IN</sub>	0 to V <sub>CC</sub> (Note 4)	V
Output voltage	(An, Bn)	V <sub>OUT</sub>	0 to V <sub>CC</sub> (Note 5)	V
			±24 (Note 6)	
Output current		I <sub>OH</sub> /I <sub>OL</sub>	±18 (Note 7)	mA
			±6 (Note 8)	
Operating temperature		T <sub>opr</sub>	-40 to 85	°C
Input rise and fall time		dt/dv	0 to 10 (Note 9)	ns/V

Note 1: The operating ranges must be maintained to ensure the normal operation of the device. Unused inputs and bus inputs must be tied to either VCC or GND. Please connect both bus inputs and the bus outputs with VCC or GND when the I/O of the bus terminal changes by the function. In this case, please note that the output is not short-circuited.

Note 2: Floating or unused control inputs must be held high or low.

Note 3: Data retention only

Note 4: OFF state

Note 5: High or low state

Note 6:  $V_{CC} = 3.0 \text{ to } 3.6 \text{ V}$ 

Note 7:  $V_{CC} = 2.3 \text{ to } 2.7 \text{ V}$ 

Note 8:  $V_{CC} = 1.8 \text{ V}$ 

Note 9:  $V_{IN} = 0.8$  to 2.0 V,  $V_{CC} = 3.0$  V



### **Electrical Characteristics**

### DC Characteristics (Ta = -40 to 85°C, 2.7 V < $V_{CC} \le 3.6$ V)

Characteristics		Symbol	Test C	Condition		Min	Max	Unit
		,			V <sub>CC</sub> (V)			
Input voltage	H-level	V <sub>IH</sub>		_	2.7 to 3.6	2.0	_	V
input voitage	L-level	V <sub>IL</sub>		_	2.7 to 3.6		0.8	V
				$I_{OH} = -100 \mu A$	2.7 to 3.6	V <sub>CC</sub> - 0.2	_	
	H-level	VoH	V <sub>IN</sub> = V <sub>IH</sub> or V <sub>IL</sub>	$I_{OH} = -12 \text{ mA}$	2.7	2.2	_	
				$I_{OH} = -18 \text{ mA}$	3.0	2.4	_	
Output voltage				$I_{OH} = -24 \text{ mA}$	3.0	2.2	_	V
				$I_{OL} = 100 \ \mu A$	2.7 to 3.6	_	0.2	
	L-level	V	$V_{OL}$ $V_{IN} = V_{IH} \text{ or } V_{IL}$	$I_{OL} = 12 \text{ mA}$	2.7	_	0.4	
	L-level	VOL		I <sub>OL</sub> = 18 mA	3.0	_	0.4	
				I <sub>OL</sub> = 24 mA	3.0	_	0.55	
Input leakage current (DIR, $\overline{\text{OE}}$ )		I <sub>IN</sub>	V <sub>IN</sub> = 0 to 3.6 V		2.7 to 3.6	_	±5.0	μА
Bushold input minimun	n drive hold		V <sub>IN</sub> = 0.8 V		3.0	75	_	
current		l (HOLD)	V <sub>IN</sub> = 2.0 V		3.0	-75	_	μΑ
Bushold input over-driv	e current to	I <sub>I (OD)</sub>	V <sub>IN</sub> = "L"→"H"		3.6	_	450	
change state (Note)			V <sub>IN</sub> = "H"→"L"		3.6	_	-450	μА
3-state output OFF state current		loz	$V_{IN} = V_{IH}$ or $V_{IL}$		2.7 to 3.6		±10.0	μА
5-State Output OFF Sta	ie cuireiii	loz	V <sub>OUT</sub> = V <sub>CC</sub> or GND		2.7 10 3.0		±10.0	μΛ
Quiescent supply curre	ent	Icc	$V_{IN} = V_{CC}$ or GND	·	2.7 to 3.6		20.0	μΑ
Increase in I <sub>CC</sub> per inp	ut	Δl <sub>CC</sub>	$V_{IH} = V_{CC} - 0.6 V$		2.7 to 3.6		750	μΑ

Note: It is a necessary electric current to change the input in "L" or "H".



## DC Characteristics (Ta = -40 to 85°C, 2.3 V $\leq$ V<sub>CC</sub> $\leq$ 2.7 V)

Characteristics		Symbol	Toot	Condition		Min	Max	Unit
Characteris	lics	Symbol	Test	Test Condition		IVIIII	IVIAX	Offic
Input voltage	H-level	V <sub>IH</sub>		_	2.3 to 2.7	1.6	_	V
input voltage	L-level	V <sub>IL</sub>		_	2.3 to 2.7		0.7	V
				$I_{OH} = -100 \mu A$	2.3 to 2.7	V <sub>CC</sub> - 0.2	_	
	H-level	VoH	V <sub>IN</sub> = V <sub>IH</sub> or V <sub>IL</sub>	$I_{OH} = -6 \text{ mA}$	2.3	2.0	_	
				$I_{OH} = -12 \text{ mA}$	2.3	1.8	_	
Output voltage				$I_{OH} = -18 \text{ mA}$	2.3	1.7	_	V
			$OL$ $V_{IN} = V_{IH} \text{ or } V_{IL}$	$I_{OL} = 100 \mu A$	2.3 to 2.7	_	0.2	
	L-level	V <sub>OL</sub>		I <sub>OL</sub> = 12 mA	2.3	_	0.4	
				I <sub>OL</sub> = 18 mA	2.3	_	0.6	
Input leakage current (DIR, $\overline{OE}$ )		I <sub>IN</sub>	V <sub>IN</sub> = 0 to 3.6 V		2.3 to 2.7	_	±5.0	μА
Bushold input minimu	m drive hold	li averes	V <sub>IN</sub> = 0.7 V		2.3	45	_	^
current		l (HOLD)	V <sub>IN</sub> = 1.6 V		2.3	-45	_	μА
Bushold input over-drive current to change state (Note)		1	V <sub>IN</sub> = "L"→"H"		2.7	_	300	^
		I <sub>I</sub> (OD)	V <sub>IN</sub> = "H"→"L"		2.7	_	-300	μА
3-state output OFF sta	ate current	I <sub>OZ</sub>	$I_{OZ}$ $V_{IN} = V_{IH} \text{ or } V_{IL}$ $V_{OUT} = V_{CC} \text{ or GND}$		2.3 to 2.7		±10.0	μА
Quiescent supply curr	ent	Icc	$V_{IN} = V_{CC}$ or GND		2.3 to 2.7	_	20.0	μΑ

Note: It is a necessary electric current to change the input in "L" or "H".



### DC Characteristics (Ta = -40 to $85^{\circ}$ C, $1.8 \text{ V} \leq \text{V}_{CC} < 2.3 \text{ V}$ )

Characterist	ics	Symbol	Test Condition		V <sub>CC</sub> (V)	Min	Max	Unit
Input voltage	H-level	V <sub>IH</sub>		_	1.8 to 2.3	0.7 × V <sub>CC</sub>	_	V
input voitage	L-level	V <sub>IL</sub>		_	1.8 to 2.3		0.2 × V <sub>CC</sub>	V
	H-level	Voh	V <sub>IN</sub> = V <sub>IH</sub> or V <sub>IL</sub>	$I_{OH} = -100 \mu A$	1.8	V <sub>CC</sub> - 0.2	_	
Output voltage				I <sub>OH</sub> = -6 mA	1.8	1.4	_	V
	Llovel	V	Ver Ver or Ve	I <sub>OL</sub> = 100 μA	1.8	_	0.2	
	L-level	V <sub>OL</sub>	$V_{IN} = V_{IH}$ or $V_{IL}$	I <sub>OL</sub> = 6 mA	1.8	_	0.3	
Input leakage current (DIR, $\overline{\text{OE}}$ )		I <sub>IN</sub>	V <sub>IN</sub> = 0 to 3.6 V		1.8	_	±5.0	μА
Bushold input minimun	n drive hold		V <sub>IN</sub> = 0.36 V		1.8	25	_	^
current		I (HOLD)	V <sub>IN</sub> = 1.26 V		1.8	-25	_	μΑ
Bushold input over-driv	Bushold input over-drive current to		V <sub>IN</sub> = "L"→"H"		1.8	_	200	^
change state (Note)		I <sub>I</sub> (OD)	V <sub>IN</sub> = "H"→"L"		1.8	_	-200	μΑ
3-state output OFF state current		loz	$V_{IN} = V_{IH}$ or $V_{IL}$		1.8	_	±10.0	μА
		32	$V_{OUT} = V_{CC}$ or GND					•
Quiescent supply curre	ent	ICC	$V_{IN} = V_{CC}$ or GND		1.8	_	20.0	μΑ

Note: It is a necessary electric current to change the input in "L" or "H".

### AC Characteristics (Ta = -40 to 85°C, input: $t_r = t_f = 2.0$ ns, $C_L = 30$ pF, $R_L = 500~\Omega$ ) (Note 1)

Characteristics	Symbol	Test Condition	V <sub>CC</sub> (V)	Min	Max	Unit
			1.8	1.5	5.0	
Propagation delay time	t <sub>pLH</sub>	Figure 1, Figure 2	$2.5 \pm 0.2$	1.0	3.0	ns
	t <sub>pHL</sub>		$3.3 \pm 0.3$	8.0	2.5	
	<b>.</b>		1.8	1.5	7.5	
3-state output enable time	t <sub>pZL</sub> t <sub>pZH</sub>	Figure 1, Figure 3	$2.5 \pm 0.2$	1.0	4.9	ns
			$3.3 \pm 0.3$	8.0	3.8	
	4		1.8	1.5	5.5	
3-state output disable time	t <sub>pLZ</sub>	Figure 1, Figure 3	$2.5 \pm 0.2$	1.0	4.2	ns
	t <sub>pHZ</sub>		$3.3 \pm 0.3$	8.0	3.7	
	+		1.8	_	0.5	
Output to output skew	tosLH	(Note 2)	$2.5 \pm 0.2$	_	0.5	ns
	t <sub>osHL</sub>		$3.3 \pm 0.3$	_	0.5	

Note 1: For  $C_L = 50$  pF, add approximately 300 ps to the AC maximum specification.

Note 2: Parameter guaranteed by design.  $(t_{OSLH} = |t_{DLHm} - t_{DLHn}|, t_{OSHL} = |t_{DHLm} - t_{DHLn}|)$ 



### Dynamic Switching Characteristics (Ta = 25°C, input: $t_r = t_f = 2.0$ ns, $C_L = 30$ pF)

Characteristics	Symbol	Test Condition	V <sub>CC</sub> (V)	Тур.	Unit
		$V_{IH} = 1.8 \text{ V}, V_{IL} = 0 \text{ V}$ (No	e) 1.8	0.25	
Quiet output maximum dynamic V <sub>OL</sub>	V <sub>OLP</sub>	$V_{IH} = 2.5 \text{ V}, V_{IL} = 0 \text{ V}$ (No	e) 2.5	0.6	V
, 01		$V_{IH} = 3.3 \text{ V}, V_{IL} = 0 \text{ V}$ (No	e) 3.3	0.8	
		$V_{IH} = 1.8 \text{ V}, V_{IL} = 0 \text{ V}$ (No	e) 1.8	-0.25	
Quiet output minimum dynamic V <sub>OI</sub>	V <sub>OLV</sub>	$V_{IH} = 2.5 \text{ V}, V_{IL} = 0 \text{ V}$ (No	e) 2.5	-0.6	V
		$V_{IH} = 3.3 \text{ V}, V_{IL} = 0 \text{ V}$ (No	e) 3.3	-0.8	
		$V_{IH} = 1.8 \text{ V}, V_{IL} = 0 \text{ V}$ (No	e) 1.8	1.5	
Quiet output minimum dynamic V <sub>OH</sub>	V <sub>OHV</sub>	$V_{IH} = 2.5 \text{ V}, V_{IL} = 0 \text{ V}$ (No	e) 2.5	1.9	V
		$V_{IH} = 3.3 \text{ V}, V_{IL} = 0 \text{ V}$ (No	e) 3.3	2.2	

Note: Parameter guaranteed by design.

### **Capacitive Characteristics (Ta = 25°C)**

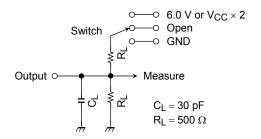
Characteristics	Symbol	Test Condition		Тур.	Unit
Characteristics	Symbol	rest condition	V <sub>CC</sub> (V)	ιyp.	Offic
Input capacitance	C <sub>IN</sub>	_	1.8, 2.5, 3.3	6	pF
Bus I/O capacitance	C <sub>I/O</sub>	_	1.8, 2.5, 3.3	7	pF
Power dissipation capacitance	C <sub>PD</sub>	f <sub>IN</sub> = 10 MHz (Note)	1.8, 2.5, 3.3	20	pF

Note: C<sub>PD</sub> is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation:

 $I_{CC (opr)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/16 \text{ (per bit)}$ 

#### **AC Test Circuit**



Parameter	Switch			
t <sub>pLH</sub> , t <sub>pHL</sub>	Open			
t <sub>pLZ</sub> , t <sub>pZL</sub>	$ \begin{array}{cccccccccccccccccccccccccccccccccccc$			
t <sub>pHZ</sub> , t <sub>pZH</sub>	GND			

Figure 1

#### **AC Waveform**

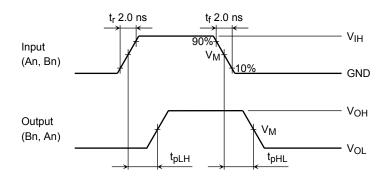


Figure 2  $t_{pLH}$ ,  $t_{pHL}$ 

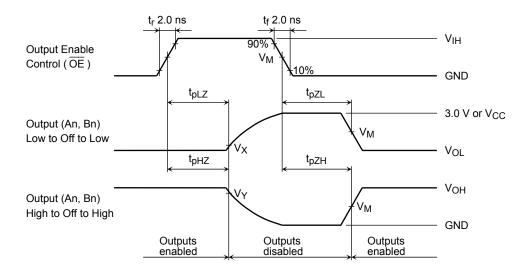


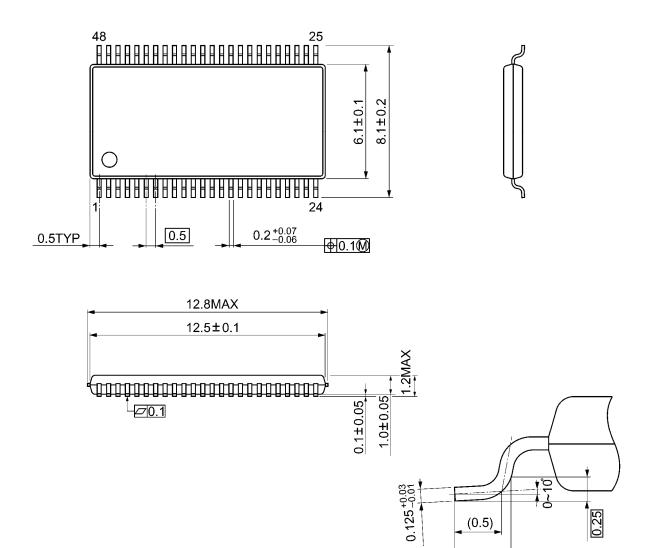
Figure 3  $t_{\text{pLZ}},\,t_{\text{pHZ}},\,t_{\text{pZL}},\,t_{\text{pZH}}$ 

Symbol		V <sub>CC</sub>	-
Syllibol	$3.3\pm0.3~\textrm{V}$	$2.5\pm0.2\textrm{V}$	1.8 V
V <sub>IH</sub>	2.7 V	V <sub>CC</sub>	V <sub>CC</sub>
V <sub>M</sub>	1.5 V	V <sub>CC</sub> /2	V <sub>CC</sub> /2
VX	V <sub>OL</sub> + 0.3 V	V <sub>OL</sub> + 0.15 V	V <sub>OL</sub> + 0.15 V
VY	V <sub>OH</sub> – 0.3 V	V <sub>OH</sub> – 0.15 V	V <sub>OH</sub> – 0.15 V

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### **Package Dimensions**

TSSOP48-P-0061-0.50A Unit: mm



Weight: 0.25 g (typ.)

0.45~0.75

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20070701-EN

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